DMMT5551/DMMT5551S

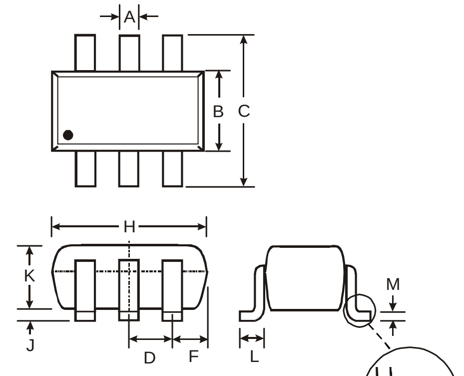
MATCHED NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

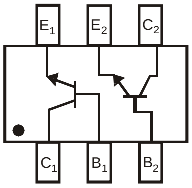
Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DMMT5401)
- Ideal for Low Power Amplification and Switching
- Intrinsically Matched NPN Pair (Note 1)
- 2% Matched Tolerance, h_{FE}, $V_{CE(SAT)}$, $V_{BE(SAT)}$
- **Lead Free/RoHS Compliant (Note 4)**
- **"Green" Device (Note 5 and 6)**

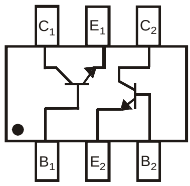
Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 7. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information: K4R & K4T, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approximate)





DMMT5551
(K4R Marking Code)



DMMT5551S
(K4T Marking Code)

SOT-26			
Dim	**Min**	**Max**	**Typ**
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
F	—	—	0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 2)	I_C	200	mA
Power Dissipation (Note 2, 3)	P_d	300	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Notes:
1. Built with adjacent die from a single wafer.
2. Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
3. Maximum combined dissipation.
4. No purposefully added lead.
5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
6. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

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Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	180	—	V	I_C = 100μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	160	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	I_E = 10μA, I_C = 0
Collector Cutoff Current	I_{CBO}	—	50	nA μA	V_{CB} = 120V, I_E = 0 V_{CB} = 120V, I_E = 0, T_A = 100°C
Emitter Cutoff Current	I_{EBO}	—	50	nA	V_{EB} = 4.0V, I_C = 0
ON CHARACTERISTICS (Note 7)					
DC Current Gain (Note 8)	h_{FE}	80 80 30	— 250 —	—	I_C = 1.0mA, V_{CE} = 5.0V I_C = 10mA, V_{CE} = 5.0V I_C = 50mA, V_{CE} = 5.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.15 0.20	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	1.0	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	6.0	pF	V_{CB} = 10V, f = 1.0MHz, I_E = 0
Small Signal Current Gain	h_{FE}	50	250	—	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f_T	100	300	MHz	V_{CE} = 10V, I_C = 10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V_{CE} = 5.0V, I_C = 200μA, R_S = 1.0kΩ, f = 1.0kHz

Notes:
7. Short duration pulse test used to minimize self-heating effect.
8. The DC Current Gain, h_{FE}, (matched at I_C = 10mA and V_{CE} = 5V) Collector Emitter Saturation Voltage, $V_{CE(SAT)}$, and Base Emitter Saturation Voltage, $V_{BE(SAT)}$ are matched with typical matched tolerances of 1% and maximum of 2%.

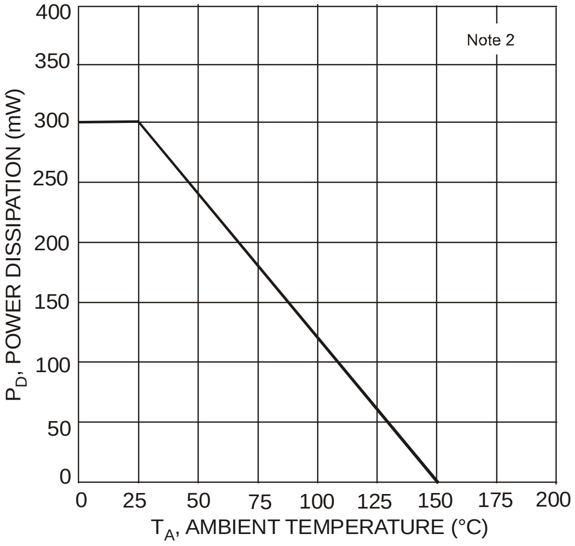

Fig. 1, Max Power Dissipation vs. Ambient Temperature

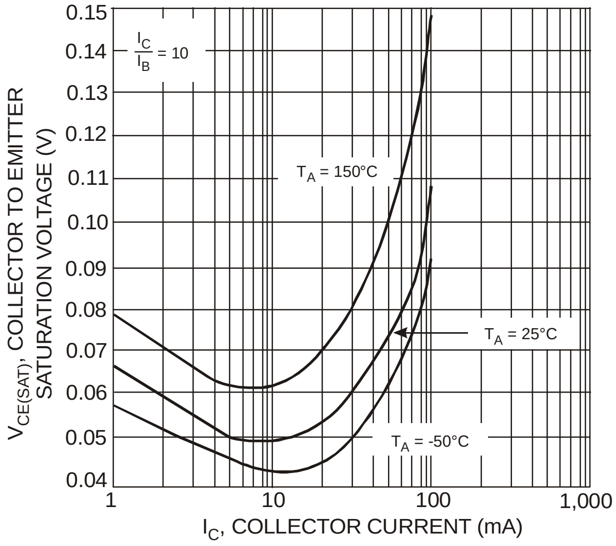

Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

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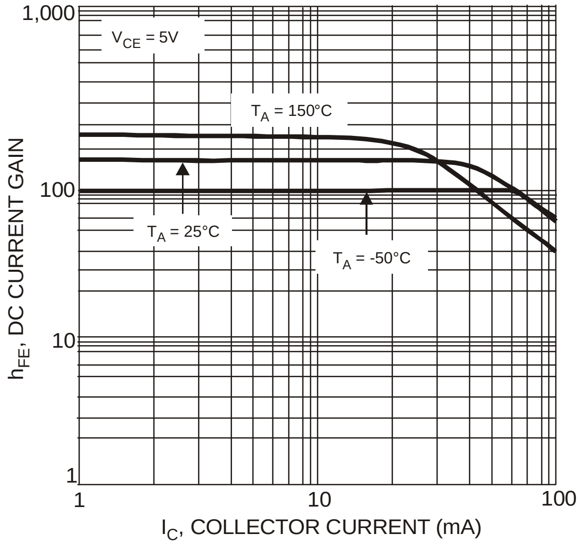


Fig. 3, DC Current Gain vs. Collector Current

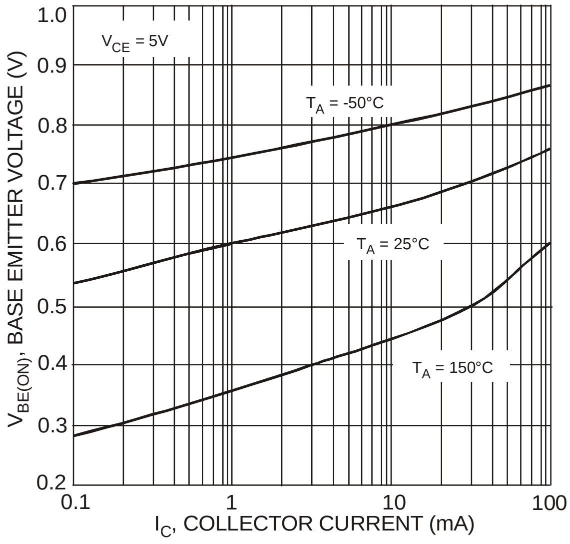


Fig. 4, Base Emitter Voltage vs. Collector Current

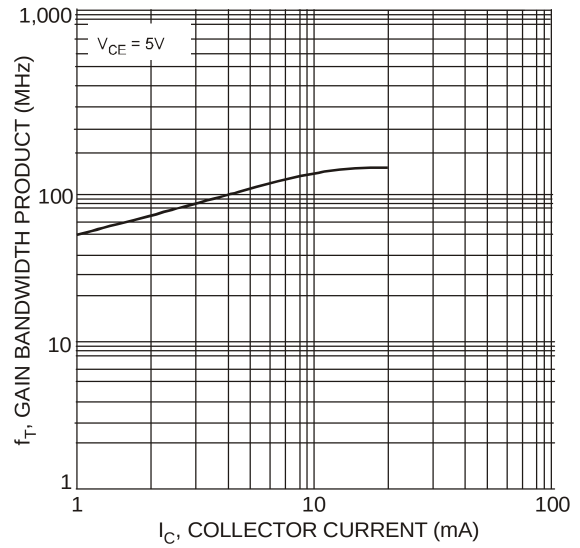


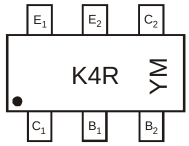
Fig. 5, Gain Bandwidth Product vs. Collector Current

Ordering Information (Note 6 & 9)

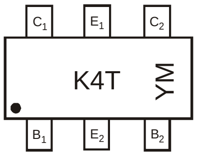
Device	Packaging	Shipping
DMMT5551-7-F	SOT-26	3000/Tape & Reel
DMMT5551S-7-F	SOT-26	3000/Tape & Reel

Notes: 9. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K4R = DMMT5551 Product Type Marking Code
YM = Date Code Marking
Y = Year ex: T = 2006
M = Month ex: 9 = September



K4T = DMMT5551S Product Type Marking Code
YM = Date Code Marking
Y = Year ex: T = 2006
M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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- Консультации по применению компонента;
- Поставка образцов и прототипов;
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